Covalent Defects of Carbon Nanotubes: New Class of High Purity, Indistinguishable Quantum Light Sources

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Solitary Dopants in Solid-State Systems



Creating quantum defect in 1D SWCNT with covalent chemistry

5);

Intrinsic Single Wall Carbon Nanotubes



Low T \rightarrow Exciton localized \rightarrow quantum dot (artificial atoms)

Defect States of Carbon Nanotubes





Outstanding Questions

- Exact chemical nature of dopant.
- Electronic structures of trap-states
- Radiative and non-radiative recombination processes

Can solitary dopant states behave as single quantum emitter at RT?

Low temperature PL, time resolve PL, & photon correlation spectroscopy studies on individual doped SWCNTs.



Emission Wavelength (nm)

without functionalization

Electronic Structure and Chemical Nature



- Low T PL \Rightarrow Sharp isolated peak spread over 1000-1400 nm range.
- Quantum Chemistry simulation ⇒ Six different chemical configurations

Electronic Structure and Chemical Nature: Quantum Chemistry Simulation



Tuning defect emission to 1.5 μ m



- Flexible diazonium chemistry allow easy attachment of dopants to larger diameter SWCNT
- Quantum defect states are created at 100-300 meV below the band edge

Emission of dopant state can be tuned from 1.0 to 1.6 μ m Cover both 1.3 and 1.55 μ m telecommunication bands











g⁽²⁾ experiment is performed at 220K to compensate for the decrease of detector efficiency.

sp³ Defects of SWCNTs: **New Building Blocks of Quantum Information Technology**



- Xiaowei He, et al., *Nat. Photonics.* **11**, 577-582 (2017).
- Xiaowei He, et al., Nat. Mater. 17, 663-670 (2018)
- Avishek Saha et al., *Nat. Chem*. 10, 1089 (2018)
- Stephen. K, Doorn, H. Htoon, S. Tretiak;, Handbook of Carbon Nanomaterials, pp. 143-189 (2019)

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Time delay (ns)

Solid-State Single Photon Emitters (SPE)



Igor Aharonovich, Dirk Englund and Milos Toth, Nature Photonic, 10, 631, 2016 and refs. therein.

	InAs Quantum Dot	Diamond NV	Defects in 2D
Count Rate	10 ⁷ Hz	10 ⁶ Hz	10 ⁵ Hz
Temperature	4K	RT	4K
Wavelength	1.3 -1.5 μm	Visible <1.0 μm	Visible <1.0 µm
Integration	Not directly compatible with Si micro-fab		

Indistinguishable Single Photons

- Spectrally indistinguishable photons are required for quantum computing and quantum repeaters.
- Indistinguishability ⇒Ultra-narrow spectral linewidth of emitters

$$\Delta E = \frac{2\hbar}{T_2} = \frac{\hbar}{T_1} + \frac{2\hbar}{T_2^*}$$

 T_2 : Over all dephasing time; T_1 : population decay time; T_2^* : pure dephasing time.

Traditional approach: Isolate the quantum emitter from environment
 ⇒ Shut down non-radiative decay channels
 ⇒ Minimize pure dephasing
 time

Shape and Width of Spectral Lines



- Low T PL spectra of polymer wrapped SWCNTs
 → Zero phonon line and acoustic phonon side band.
- ZPL Line widths of 200-400 μeV

Shape and Width of Spectral Lines



• Environment has strong effect on linewidths

Shape and Width of Spectral Lines



Surfactant (DOC) wrapped (6,5) tubes on Polymer (PS) substrate





Narrowest linewidth achieved 98.5 μeV
 PL lifetime T₁ ~ 1.5 ns. Approaching theoretical limit of 3 ns

$$\Delta E = \frac{2\hbar}{T_2} = \frac{\hbar}{T_1} + \frac{2\hbar}{T_2^*}$$

Linewidth is dominated by pure dephasing T₂^{*}

New Paths to Photon Indistinguishability: Plasmonic Enhancement

Exploit Plasmonic Effect to enhance radiative decay rate so that it would dominate over all the other processes.



- Plasmonic cavity Au nanocube /Al₂O₃/SWCNT/Al₂O₃/Au Mirror
- Gap size of $5nm \Rightarrow$ Field enhancement 800
- Cavity resonance ~ 1200 nm
- SWCNTs are spread randomly over the nanocube array.
- High density nanocube array with filling factor of 65% ensure coupling to the SWCNT.
- PL of SWCNT coupled to nanocube array strongly enhanced compared to that of uncoupled SWCNTs.

Plasmonic Enhancement of PL Emission



Room Temperature Experiment

- PL intensity at saturation is enhanced by 52 fold
- PL lifetime of uncoupled SWCNTs 588 ± 10 ps
- PL lifetime of coupleds SWCNT 11 \pm 3 ps
- Decay rate enhancement ~ $\gamma_{on,RT}/\gamma_{off,RT} = 53$

$$F_{p} = 0.75 \left(\frac{\gamma_{\text{on}}}{\gamma_{\text{off}}} - 1\right) \eta_{\text{off}}^{-1}$$
$$\eta_{\text{on}} = \frac{(Fp+1) \gamma_{\text{R}}}{\gamma_{\text{on}}} = \frac{(Fp+1) \gamma_{\text{off}} \eta_{\text{off}}}{\gamma_{\text{on}}} = \frac{(F_{p}+1) \eta_{\text{off}}}{\frac{\gamma_{\text{on}}}{\gamma_{\text{off}}}},$$

Quantum yield of uncoupled emitter: $\eta_{off} = 13\%$

Purcell Enhancement Factor F_p = 300

Plasmonic Enhancement of PL Emission



Low Temperature Experiment

- PL intensity at saturation is enhanced by 133 fold
- PL lifetime of uncoupled SWCNT 726 ± 10 ps
- PL lifetime of coupled SWCNT 10 \pm 3 ps
- Decay rate enhancement ~ 73

Strong rate enhancement 1.3 GHz Single photon emission

Purcell Enhancement Factor F_p = 450 Cavity enhanced quantum yield = 74%

Alternative Path to Photon Indistinguishability



$$\Delta E = \frac{2\hbar}{T_2} = \frac{\hbar}{T_1} + \frac{2\hbar}{T_2^*}$$

- Low T intrinsic linewidths: ΔE = 105 \pm 5 μeV
- population decay time: $T_1 = 10$ ps.

•
$$\frac{\hbar}{T_1}$$
 =60 µeV; $\frac{2\hbar}{T_2^*}$ =82 µeV

Single photon indistinguishability $T_2/2T_1 = 0.63$ is achievable !

Hanbury-Brown-Twiss (HBT) Experiment



Hong-Ou-Mandel (HOM) Experiment



- Split the excitation pulse into two pulses with $\Delta t = 2.6$ ns
- Add a BS and a delay line of the same Δt to the detection channel
- Induce two photon interference at the second BS
- When HWP is turned to rotate polarization of one channel perpendicular to another interference will be destroyed.

Hong-Ou-Mandel (HOM) Experiment



Quantum Defect @ 1234 nm (Resonance with cavity mode) two-photon interference visibility 0.78 ± 0.08

Quantum Defect @ 1304 nm (Off resonance with cavity) Single Photon Indistinguishability

 $\textbf{0.40} \pm \textbf{0.04}$



Summary: Demonstration of Photon Indistinguishability

Quantum defect – plasmonic cavity coupling

On-chip, telecom band, RT quantum light source with 1.3GHz brightness.



Cavity enhanced QY of 74% and Purcell factor of 415 On demand single photon source with 99% single photon purity and Single photon indistinguishability with 78% fringe visibility



Indistinguishable single photons at telecom O-band from sp³ functionalized carbon nanotubes coupled to plasmonic nanocavities

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Nano Letter 10.1021/acs.nanolett.9b04069





A. Srivastava et al., *PRL.*, **2008**, 101, 087402

- Band edge exciton (E₁₁) is four fold degenerated.
- Application of magnetic field parallel to the tube axis can lift this degeneracy and brighten the dark exciton state.

Can similar excitonic fine structure exit in defect states of CNT?



Opportunity of optical manipulation of spin or valley degree of freedom.

4-Methoxybenzene diazonium doped (6,5) CNT



• No splitting was observed in 75% of the defect states





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- <5% of the defect emission peaks split into two peaks

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- <5% of the defect emission peaks split into two peaks
- 20% of the defects show 3 or more peaks at 8.5 T



140

1.10



- Defect bound singlet exciton state can get into close vicinity of free 1 D triplet excitons
- Magnetic field can induce the mixing between the two
- Triplet states as a result got brightened.



Photonic, Plasmonic, and Electronic Integration



Plasmonic Antenna Array: Stefan Strauf, Stevens Institute of Technology



Waveguide Integrated Electrically Driven Single Photon Sources



Ralph Krupke (Karlsrue Institute of Technology)

Electrically driven SPS operating at RT and 1.55 µm Integrated with wave guide and single photon detectors for proof of principle quantum photonic experiments



Khasminskaya, S. et al. Fully integrated quantum photonic circuit with an electrically dr en light source. Nat. Photon. 10, 727-732 (2016)

Thanks for your Attention

